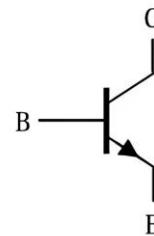


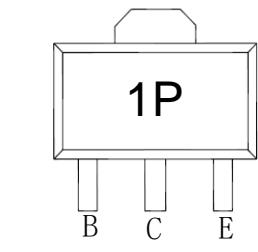
Features

- Epitaxial planar die construction
- Complementary PNP Type available(PXT2907A)



SOT-89-3L top view

Schematic diagram



Marking and pin assignment



Halogen-Free

Maximum Ratings (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	75	V
V _{CEO}	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current	600	mA
P _C	Collector Power Dissipation	0.5	mW
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

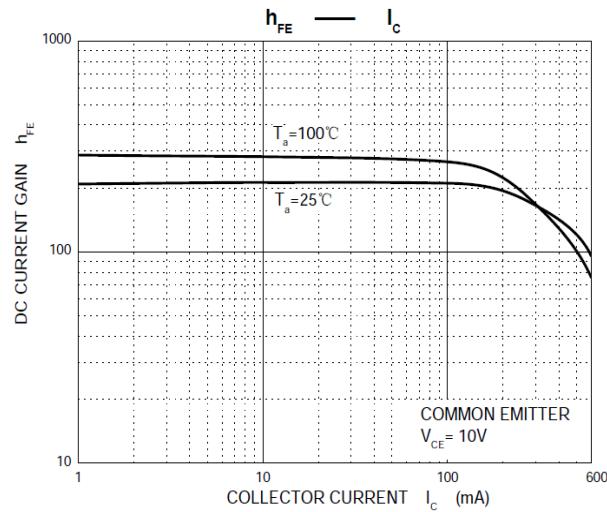
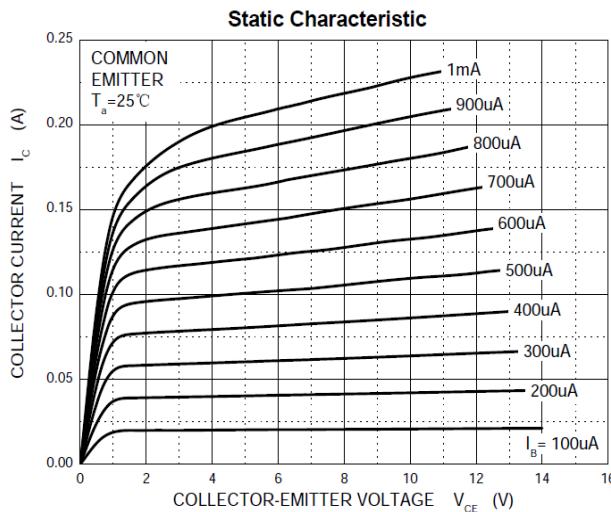
Ordering Information (Example)

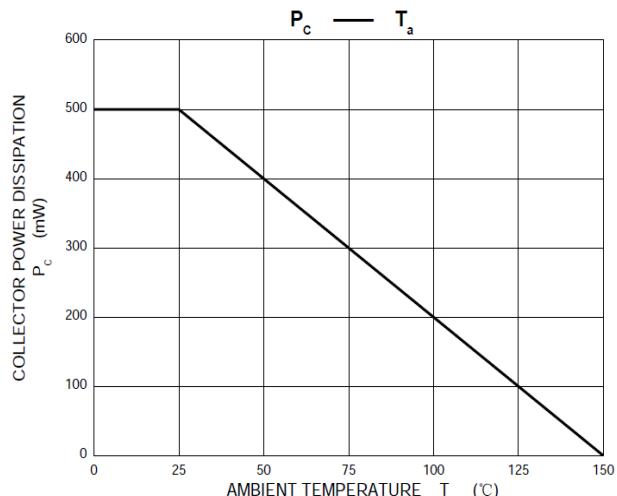
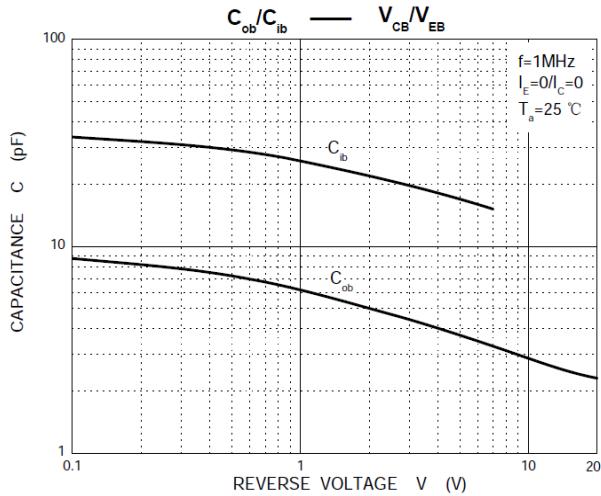
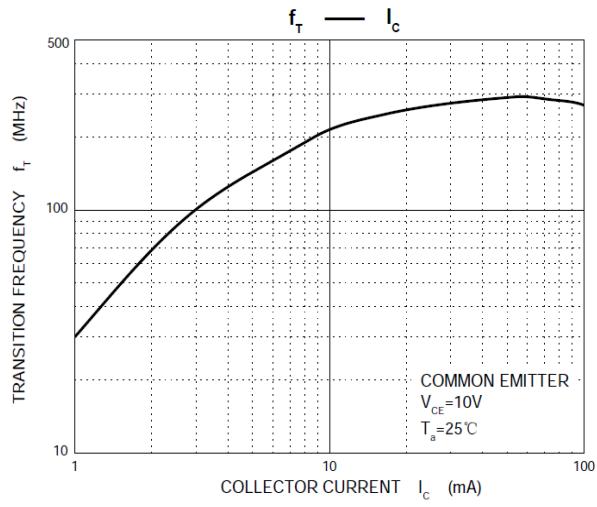
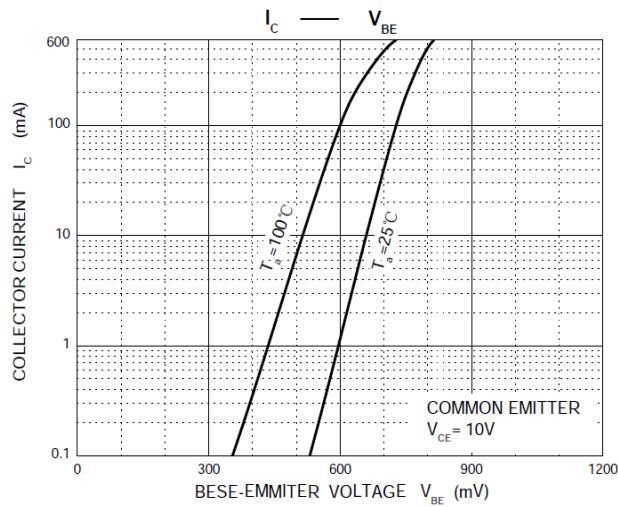
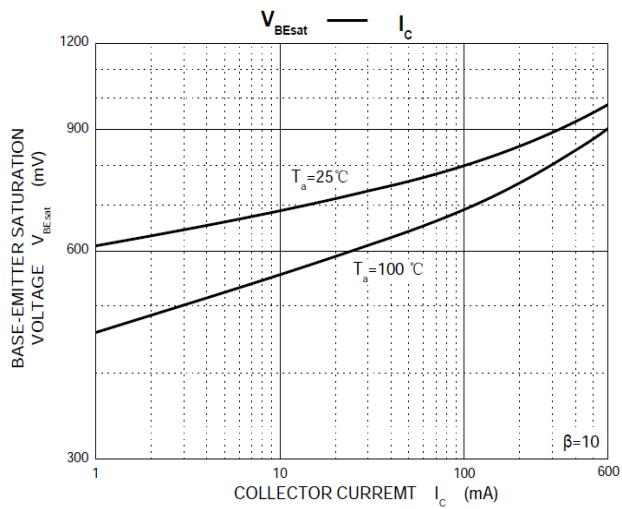
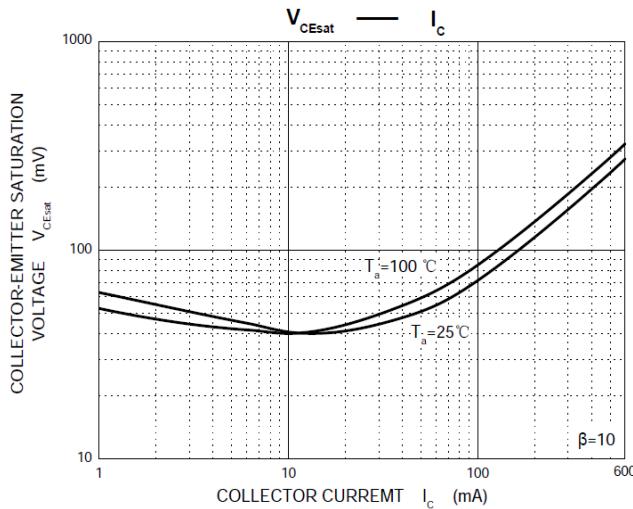
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
PXT2222A	SOT-89-3L	1P	1,000	10,000	40,000	7" reel

Electrical Characteristics (Ta=25°C unless otherwise specified)

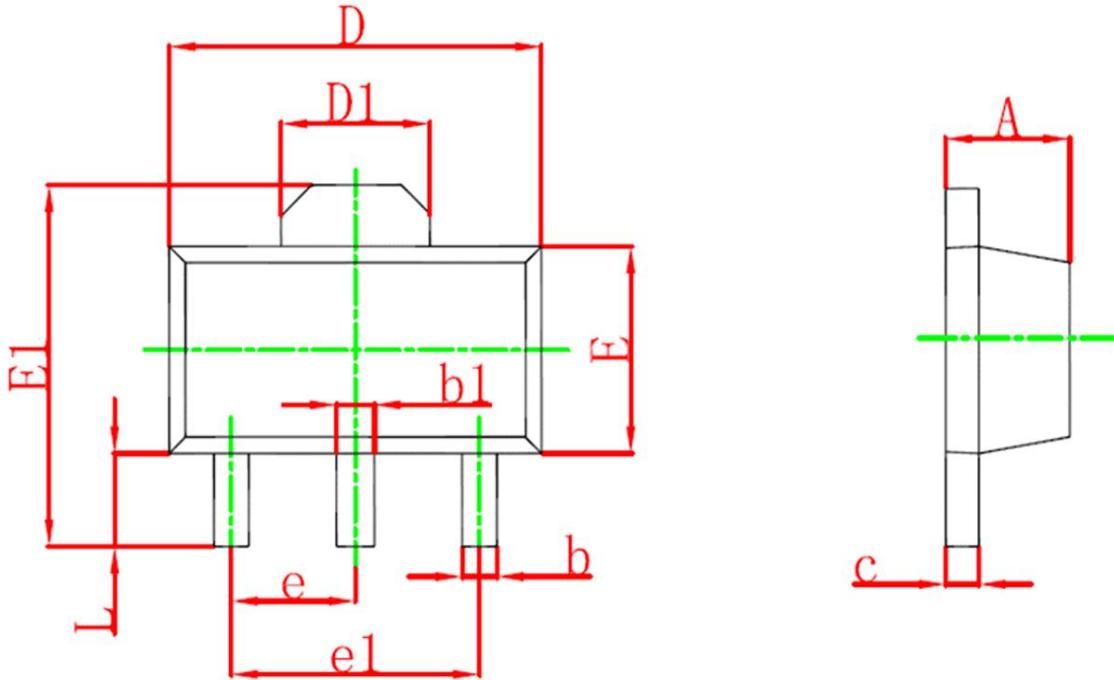
Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =10μA, I _E =0	75	--	--	V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA, I _B =0	40	--	--	V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =10μA, I _C =0	6	--	--	V
I _{CBO}	Collector cut-off current	V _{CB} =60V, I _E =0	--	--	0.01	μA
I _{EBO}	Emitter cut-off current	V _{EB} =5V, I _C =0	--	--	0.01	μA
H _{FE(1)}	DC current gain	V _{CE} =10V, I _C =0.1mA	35	--	--	--
H _{FE(2)}		V _{CE} =10V, I _C =1mA	50	--	--	
H _{FE(3)}		V _{CE} =10V, I _C =10mA	75	--	--	
H _{FE(4)}		V _{CE} =10V, I _C =150mA	100	--	300	
H _{FE(5)}		V _{CE} =1V, I _C =150mA	50	--	--	
H _{FE(6)}		V _{CE} =10V, I _C =500mA	40	--	--	
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =500mA, I _B =50mA			1	V
		I _C =150mA, I _B =15mA	--	--	0.3	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =500mA, I _B =50mA			2	V
		I _C =150mA, I _B =15mA	0.6	--	1.2	V
C _{ob}	Collector output capacitance	V _{CB} =10V, I _E =0, f=1MHz	--	--	8	pF
t _d	Delay time	V _{CC} =30V, I _C =150mA	--	--	10	ns
t _r	Rise time	V _{BE(off)} =0.5V, I _{B1} =15mA	--	--	25	ns
t _s	Storage time	V _{CC} =30V, I _C =150mA	--	--	225	ns
t _f	Fall time	I _{B1} =I _{B2} =15mA	--	--	60	ns
f _T	Transition frequency	V _{CE} =10V, I _C =20mA, f=100MHz	300	--	--	MHz

Typical Characteristics





SOT-89-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions in Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF		0.061 REF	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP		0.060 TYP	
e1	3.000 TYP		0.118 TYP	
L	0.900	1.200	0.035	0.047